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⑤④ **Coating electronic substrates with silica derived from silazane polymers.**

⑤⑦ A silica coating is formed on an electronic substrate by applying a silazane polymer on the substrate and converting it to silica by heating in an oxidizing environment. The resultant thick planarizing coatings are useful as protective coatings and dielectric inner layers.

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The present invention relates to a method of applying silica coatings on electronic substrates wherein silazane polymers are used as precursors to silica coatings.

Various methods for the application of ceramic coatings on electronic devices are known in the art. For instance, it is known to use gaseous precursors in a variety of vapor deposition processes to produce coatings of silica, silicon nitride, silicon oxynitride and silicon carbide. These coatings are taught to be useful as protective and dielectric layers.

Similarly, the use of polymeric precursors for depositing ceramic coatings on electronic devices is also known in the art (Haluska et al. in U.S. Patents 4,749,631 and 4,756,977). The Accuglass™ product literature also disclose silica coatings produced by applying solutions of silica precursors to electronic devices and then heating the coated devices to convert the precursors to silica. These references, however, fail to disclose or suggest the use of polysilazanes as the silica precursors.

Finally, the use of polysilazanes for applying silicon and nitrogen containing ceramic coatings on electronic devices is also known in the art. For example, Haluska et al. in U.S. Patents 4,756,977 and 4,826,733 teach forming ceramic coatings by applying coatings of silicon and nitrogen containing polymers, such as polysilazanes, on such devices and then heating the coated devices in an inert atmosphere. Since the coatings are heated in an inert atmosphere, the nitrogen is maintained in the coating and silica is not formed.

We have now found that silica coatings derived from silazane polymers can be applied on electronic substrates. Since the resultant coatings are thick, planar and defect free, they can be used as protective and dielectric layers.

The present invention relates to a method for depositing a silica coating on an electronic substrate. The method comprises first applying a coating comprising a silazane polymer on an electronic substrate. The coated substrate is then heated in an oxidizing atmosphere at a temperature sufficient to convert the silazane polymer to a silica coating.

The present invention introduces preceramic silazane polymers that can be used to form silica coatings on electronic substrates. This was particularly unexpected since it was not known whether silazane polymers could be converted to silica on electronic substrates without damaging the substrates and whether such coatings would have useful effects in the electronics industry.

As used in the present invention, the expression "silica" refers to those pyrolyzed materials containing Si-O-Si bonds which may or may not be fully free of residual Si-C, Si-H, Si-OH, Si-OC, Si-N, N-H and/or N-C but which are otherwise ceramic in character. The expression "planarizing coating" refers to a coating which is less irregular than the surface prior to application of the coating. The expression "electronic substrate" includes silicon based devices, gallium arsenide based devices, focal plane arrays, opto-electronic devices, photovoltaic cells, optical devices, flat panel displays and integrated circuits at both wafer and assembly stage. Examples of such substrates include transistor-like devices, capacitor and capacitor-like devices, multilayer devices, 3-D devices, silicon on insulator devices and super lattice devices.

The process of the present invention involves applying a coating comprising a silazane polymer on an electronic substrate and then heating the coated substrate in an oxidizing atmosphere at a temperature sufficient to convert the silazane polymer to a silica coating.

The polysilazanes (or silazane polymers) useful in this invention are generally well known in the art and their structure is not particularly critical. The polysilazanes of this invention generally contain units of the type $[R_2SiNH]$, $[RSi(NH)_{1.5}]$ and/or $[R_3Si(NH)_{1.2}]$ wherein each R is independently selected from hydrogen; alkyl radicals of 1 to 20 carbon atoms; aryl radicals and alkenyl radicals. Naturally, the polysilazanes useful in this invention may contain other silazane units. Examples of such units include $[MeSi(NH)_{1.5}]$, $[Me_2SiNH]$, $[ViSi(NH)_{1.5}]$, $[Vi_2SiNH]$, $[PhMeSiNH]$, $[PhViSiNH]$, $[MeViSiNH]$, $[HSi(NH)_{1.5}]$ and $[H_2SiNH]$. As used herein, Vi is vinyl, Ph is phenyl and Me is methyl. Mixtures of these polysilazanes may also be employed in the practice of this invention.

The polysilazanes of this invention can be prepared by techniques well known in the art. The actual method used to prepare the polysilazane is not critical. Suitable preceramic silazane polymers or polysilazanes may be prepared by the methods of U.S. Patents 4,540,803 and 4,543,344. Other polysilazanes suitable for use in this invention can be prepared by the methods of U.S. Patents 4,312,970, 4,340,619, 4,395,460 and 4,404,153. Suitable polysilazanes also include those prepared by U.S. Patents 4,482,689 and 4,397,828. Still other polysilazanes include those of European Patent 0 351 747; U.S. Patent 4,543,344; European Patent 0 332 374; U.S. Patents 4,656,300, 4,689,252 and 5,030,744.

The preferred polysilazanes are those which have no carbon in the repeating units of the polymer since the resultant coatings have little carbon contamination. End blocking groups such as $Me_3Si(NH)_{1/2}$ are acceptable in such polymers since they will be removed during the subsequent pyrolysis steps.

The most preferred polymers used herein are those of Gaul in U.S. Patent 4,340,619 and those of Cannady in U.S. Patent 4,540,803. The silazane polymers of Gaul are prepared by contacting and reacting in an inert,

essentially anhydrous atmosphere a chlorine containing disilane or mixture of chlorine containing disilanes of the general formula $(Cl_xR_ySi)_2$ with a disilazane having the general formula $(R'_3Si)_2NH$ at a temperature in the range of 25°C. to 300°C. while distilling volatile byproducts, wherein R is vinyl, an alkyl group of 1-3 carbon atoms or a phenyl group; R' is vinyl, hydrogen an alkyl group of 1-3 carbon atoms or a phenyl group; x has a value of 0.5-3; y has a value of 0-2.5 and the sum of $x+y$ equals 3.

The chlorine containing disilanes of Gaul have the general formula $(Cl_xR_ySi)_2$ where R is vinyl, an alkyl group of 1-3 carbon atoms or a phenyl group. Thus, the R groups are independently selected from methyl, ethyl, propyl, vinyl and phenyl. Examples of these chlorine containing disilanes include $[Cl(CH_3)_2Si]_2$, $[Cl_2CH_3Si]_2$, $[Cl_2C_2H_5Si]_2$, $[Cl(C_6H_5)_2Si]_2$, $[Cl_2CH_2=CHSi]_2$, $Cl(CH_3)_2SiSi(CH_3)Cl_2$ and $Cl(C_6H_5)_2SiSi(CH_3)_2Cl$.

Monosilanes may also be used in admixture with the above described chlorine containing disilanes. Examples of such monosilanes include CH_3SiCl_3 , $H(CH_3)_2SiCl$, $(CH_3)_2SiCl_2$, $(CH_3)_3SiCl$, $(CH_2=CH)(CH_3)_2SiCl$, $(C_2H_5)_2SiCl_2$, $C_6H_5SiCl_3$ as well as $(C_6H_5)_2SiCl_2$ and $(C_6H_5)_3SiCl$.

The disilazane used by Gaul has the formula $(R'_3Si)_2NH$, where R' is vinyl, hydrogen, an alkyl group of 1-3 carbon atoms or a phenyl group. Thus, the R' groups are independently selected from hydrogen, methyl, ethyl, propyl, vinyl and phenyl. Examples of suitable disilazanes include $[(CH_3)_3Si]_2NH$, $[C_6H_5(CH_3)_2Si]_2NH$, $[(C_6H_5)_2CH_3Si]_2NH$, $[CH_2=CH(CH_3)_2Si]_2NH$, $[CH_2=CH(CH_3)C_6H_5Si]_2NH$, $[CH_2=CH(C_6H_5)_2Si]_2NH$, $[CH_2=CH(C_2H_5)_2Si]_2NH$, $[H(CH_3)_2Si]_2NH$ and $[CH_2=CH(C_6H_5)C_2H_5Si]_2NH$.

An especially preferred embodiment of the Gaul inventions involve the reaction of methylchlorosilanes with hexamethyldisilazane to produce methylpolydisilazane. The above reactants are brought together in an inert, essentially anhydrous atmosphere. By "inert", it is meant that the reaction is carried out under a blanket of inert gas such as argon, nitrogen or helium. What is meant by "essentially anhydrous" is that the reaction is preferably carried out in an absolutely anhydrous atmosphere but minute amounts of moisture can be tolerated.

When the reactants are contacted with each other an intermediate amino compound is formed. Upon continued heating, R_3SiCl is distilled from the reaction mixture and the silazane polymer formed. As the temperature of reaction is raised, more condensation takes place and crosslinking occurs. This control allows one to stop the reaction at any point to obtain almost any desired viscosity. The desired temperature range for the reaction is 25°C. to 300°C. with a temperature in the range of 125°C. to 300°C. being more preferred. The length of time that the reaction requires depends on the temperature employed and the viscosity one wishes to achieve.

The above described silazane polymers of Gaul may have a relatively high chloride ion content and it is preferred that such concentration be lowered before use in the present invention. A suitable method for such removal is described in U.S. Patent 4,772,516. The method described therein comprises treating the polymer with ammonia for a time sufficient to remove the chlorine.

The silazane polymers of Cannady are prepared by a method which comprises contacting and reacting in an inert essentially anhydrous atmosphere, trichlorosilane with a disilazane at a temperature in the range of 25°C. to 300°C. while distilling volatile byproducts. The disilazane used in the process has the formula $(R_3Si)_2NH$ where R is selected from the group consisting of vinyl, hydrogen, phenyl and alkyl radicals containing 1 to 3 carbon atoms.

The trichlorosilane is treated with the disilazane in sufficient amounts to react with all of the chlorine in the chlorine containing silane. This is usually an equimolar amount based on the chlorine content of the trichlorosilane.

The disilazane used in the Cannady invention has the formula $(R_3Si)_2NH$, where R is vinyl, hydrogen, an alkyl group of 1-3 carbon atoms or a phenyl group. Thus, the R' groups are independently selected from hydrogen, methyl, ethyl, propyl, vinyl and phenyl. Examples of suitable disilazanes include $[(CH_3)_3Si]_2NH$, $[C_6H_5(CH_3)_2Si]_2NH$, $[(C_6H_5)_2CH_3Si]_2NH$, $[CH_2=CH(CH_3)_2Si]_2NH$, $[CH_2=CH(CH_3)C_6H_5Si]_2NH$, $[CH_2=CH(C_6H_5)_2Si]_2NH$, $[CH_2=CH(C_2H_5)_2Si]_2NH$, $[H(CH_3)_2Si]_2NH$ and $[CH_2=CH(C_6H_5)C_2H_5Si]_2NH$.

An especially preferred embodiment of the Cannady invention involves the reaction of trichlorosilane with hexamethyldisilazane to produce hydridopolysilazane.

The above reactants are brought together in an inert, essentially anhydrous atmosphere. By "inert", it is meant that the reaction is carried out under a blanket of inert gas such as argon, nitrogen or helium. What is meant by "essentially anhydrous" is that the reaction is preferably carried out in an absolutely anhydrous atmosphere but minute amounts of moisture can be tolerated.

When the reactants are contacted with each other an intermediate amino compound is formed. It is preferred that the reactants are brought together in such a manner to keep the initial reaction exotherm to a minimum. Upon continued heating additional amino compound is formed and, with further heating, R_3SiCl is distilled from the reaction mixture and the silazane polymer formed. For best results, the rate of heating should be controlled at a rate of less than 1°C./min. A heating rate of 0.5°C./min. or less is preferred. As the temperature

of reaction is raised, more condensation takes place and crosslinking occurs with residual R_3Si that is not distilled from the mixture acting as a chain stopper. This control allows one to stop the reaction at any point to obtain almost any desired viscosity. The desired temperature range for the reaction is 25°C. to 300°C. with a temperature in the range of 125°C. to 275°C. being more preferred. The length of time that the reaction requires depends on the temperature employed and the viscosity one wishes to achieve.

Although only several polymers are described above, nearly any polysilazane may be used herein.

The above silazane is first applied to the substrate to form a preceramic coating. Although any conventional technique may be used, it is particularly preferred to coat the substrate with a solution comprising a solvent and the silazane. Removal of the solvent by evaporation or a similar technique yields the preceramic coating. Other equivalent methods such as melt coating, however, are also contemplated herein.

If the above solution method is used, the silazane is first dissolved in a solvent. Various facilitating measures such as stirring and/or heating may be used to aid in the dissolution. Solvents which may be used include any which will dissolve the silazane to form a solution or suspension without affecting the coating. These solvents can include aromatic hydrocarbons such as xylene, benzene or toluene; alkanes such as n-heptane, decane or dodecane; ketones; esters; glycol ethers or cyclic dimethylpolysiloxanes, in an amount sufficient to dissolve the above materials. Generally, enough of the above solvent is used to form a 0.1-50 weight percent solution.

If the above solution method is used, the coating solution is applied by techniques such as spin coating, dip coating, spray coating or flow coating. Evaporation of the solvent by any suitable means such as simple air drying by exposure to an ambient environment or by the application of a vacuum or mild heat yields the desired preceramic coating.

The resultant coating is then heated in an oxidizing environment which causes hydrolysis of the SiN bonds and loss of nitrogen to thereby facilitate conversion of the silazane to silica. In addition, other functional groups on silicon are removed by such an environment. Oxidizing environments such as those comprising air, O_2 , ozone, moisture, oxygen plasma, ammonia and amines may be used. Although the preferred environment will vary depending on the silazane, it is often preferred to heat under a wet ammonia atmosphere (ammonia and water vapor) and then under a dry ammonia atmosphere to effect removal of any remaining Si-OH groups and/or other functionality.

The silazane is subjected to the reactive environments at a temperature sufficient for ceramification. Generally, this temperature is 20 to 1000°C. depending on the reactive atmosphere. Preferred temperatures are in the range of 50 to 800°C. Higher temperatures usually result in quicker and more complete ceramification, but said temperatures may also have detrimental effects on various temperature sensitive substrates. For temperature sensitive substrates, temperatures in the range of 100 to 500°C. are often preferred. The silazane coatings are usually subjected to these temperatures for a time sufficient to ceramify the coating, generally up to 6 hours, with a range of 2-4 hours being preferred.

Any source of heat such as a hot plate, a convection oven, rapid thermal processing or radiant or microwave energy can be used during the pyrolysis step.

By the above methods, a silica planarizing coating is produced on the substrate. The coating smooths the irregular surfaces of various substrates and has excellent adhesion. In addition, this coating can be quite thick (eg., > 0.5 micrometers). This coating may also be covered by other coatings such as further SiO_2 coatings, SiO_2 /modifying ceramic oxide layers, silicon containing coatings, silicon carbon containing coatings, silicon nitrogen containing coatings, silicon nitrogen carbon containing coatings and/or diamond like carbon coatings. Such multilayer coatings are taught in U.S. Patent No. 4,973,526.

The following examples are provided so that one skilled in the art may more readily understand the invention.

Example 1

Hydridopolysilazane polymer produced by the method of U.S. Patent No 4,540,803 was diluted to 10 wt. % in toluene. Several drops of this solution were applied to the surface of a 2.54 cm (1 inch) square silicon wafer and the wafer was spun at 3000 RPM for 35 seconds. The coated wafer was then pyrolyzed at 400°C. for 3 hours in air. The resultant coating was 0.4751 micrometers thick and had a refractive index of 1.459 at 8300 lambda (silica = 1.462).

FTIR spectra were run before and after pyrolysis. A comparison of these spectra showed that most of the SiH and SiOH had been removed by heating but that some Si- CH_3 remained.

Examples 2-4

Hydridopolysilazane polymer produced by the method of U.S. Patent No 4,540,803 was diluted in toluene to the concentration indicated in Table 1. Several drops of this solution were applied to the surface of a 2.54 cm (1 inch) square silicon wafer and the wafer was spun at 3000 RPM for 35 seconds. The coated wafer was then pyrolyzed as indicated in Table 1. The results are set forth in Table 1.

TABLE 1

Ex No	Conc (wt %)	Pyrolysis Conditions	Results
2	10	2 hr/175°C./moist air	Little if any reaction occurred
3	10	3 hr/180°C./ozone	FTIR - SiH gone; some SiOH still present; coating thickness = 0.1912 micrometers; RI = 1.443 (8300 lambda)
4	25	3 hr/400°C./wet ammonia and 2 hr/400°C./ammonia	FTIR - SiH and SiOH gone; coating thickness = 0.9349 micrometers; RI = 1.472 (4050 lambda)

Example 5

Hydridopolysilazane polymer produced by the method of U.S. Patent No 4,540,803 was diluted to 10 wt. % in heptane. Several drops of this solution were applied to the surface of a 2.54 cm (1 inch) square silicon wafer and a 14011B CMOS device. The wafer and device were spun at 3000 RPM for 20 seconds. The coated wafer and device were then pyrolyzed at 175°C. for 1 hour in 4.5-4.7% ozone. A comparison of the FTIR spectra before and after conversion indicated that all of the organic and amine substitution had disappeared, but a lot of SiOH was still present.

In order to remove the silanol functionality, the coated wafer and device were heated in aqueous ammonia for 3 hours at 175°C. The FTIR spectra indicated that a majority of the silanol had been removed. The CMOS device was operational after coating. The resultant coating was 0.2944 micrometers thick and had a refractive index of 1.455 at 5040 lambda.

Example 6

Hydridopolysilazane polymer produced by the method of U.S. Patent No 4,540,803 was diluted to 10 wt. % in xylene/toluene. Several drops of this solution were applied to the surface of a 10.2 cm (4 inch) square silicon wafer which was spun at 3000 RPM for 35 seconds. The coated wafer was then pyrolyzed at 350-380°C. for 4 hours in aqueous ammonia vapor. A comparison of the FTIR spectra before and after conversion indicated that the coating had been converted to silica. The coating was 0.1130 micrometers thick and had a refractive index of 1.416 at 5040 lambda.

Example 7

Hydridopolysilazane polymer produced by the method of U.S. Patent No 4,540,803 was diluted to 22 wt. % in heptane. Several drops of this solution were applied to the surface of a 2.54 cm (1 inch) square silicon wafer and a 5.1 cm (2 inch) square alumina substrate. The wafer and substrate were spun at 3000 RPM for 20 seconds. The coated wafer was then pyrolyzed at 800°C. for 1 hour in air. FTIR spectra were run before and after pyrolysis and they showed conversion to silica. The coatings were 2.0745 micrometers thick after 2 coats and had a refractive index of 1.458 at 4050 lambda. The coatings on the silicon and alumina substrates were examined at a magnification of 1000X and found to have no cracks.

Claims

1. A method for depositing a silica coating on an electronic substrate comprising:
applying a coating comprising a silazane polymer on an electronic substrate and



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Application Number
EP 94 30 0585

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl. 5)
X	EP-A-0 218 117 (ALLIED CORPORATION) * the whole document *	1-4,7	H01L21/316
X	--- PATENT ABSTRACTS OF JAPAN vol. 17, no. 84 (P-1490) 19 February 1993 & JP-A-04 285 958 (TOKYO OHKA KOGYO) 12 October 1992 * abstract *	1-4	
P,X	--- PATENT ABSTRACTS OF JAPAN vol. 17, no. 321 (C-1072) 18 June 1993 & JP-A-05 032 410 (TOKYO OHKA KOGYO) * abstract *	1-5	
			TECHNICAL FIELDS SEARCHED (Int. Cl. 5)
			H01L
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 28 November 1994	Examiner LIBBERECHT, E
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